Antiferroelectric energy storage film

Are antiferroelectric materials suitable for energy storage applications?

Antiferroelectric materials with double hysteresis loops are attractive for energy storage applications, which are becoming increasingly important for power electronics nowadays. Among them, AgNbO 3 based lead-free ceramics have attracted intensive interest as one of promising environmental-friendly candidates.

Can PZ-based anti-ferroelectric thin films be used for electrical energy storage?

During the past decade, numerous studies have been reported to develop high-performance PZ-based anti-ferroelectric thin films for electrical energy storage applications.

What are pbzro 3 based anti-ferroelectric films?

Compared with the lead-free anti-ferroelectric materials,PbZrO 3 (PZ)-based anti-ferroelectric films are defined as promising electrical energy storage devices for pulsed power systemsdue to their ultrahigh energy storage density.

Are antiferroelectric oxides a multifunctional material?

Antiferroelectric (AFE) oxides are multifunctional materialsthat have attracted much attention due to their unique field-induced phase transition 7,8. The field-induced strain could reach 1.1% during the AFE-FE phase transition 9,much larger than the piezoelectric strain in most of the ferroelectric materials.

Are antiferroelectric ceramics tunable domain switching?

Ge, G. et al. Tunable domain switching features of incommensurate antiferroelectric ceramics realizing excellent energy storage properties. Adv. Mater. 34, e2201333 (2022). Wang, T. et al. Giant energy storage of flexible composites by embedding superparaelectric single-crystal membranes. Nano Energy 113, 108511 (2023).

Do all-inorganic flexible films have energy storage properties?

Cite this: ACS Appl. Mater. Interfaces 2022, 14, 25, 28997-29006 With the increasingly high requirements for wearable and flexible devices, traditional inorganic capacitors cannot meet the flexible demand of next-generation electronic devices. In this work, the energy storage property of all-inorganic flexible films has been systematically studied.

In this study, epitaxial antiferroelectric PbHfO 3 films with different orientations are fabricated, in which remarkable anisotropies of polarization and energy storage properties ...

The utilization of AgNbO 3 film in dielectric energy storage poses challenges due to its susceptibility to impurity phase formation, which compromises its antiferroelectric ...

Here, we provide an overview of the state-of-the-art lead-free Nb-based films for energy storage applications, which include K0.5Na0.5NbO3-based, K0.5Na0.5Bi4NbTi3O15-based, AgNbO3 ...

Benefitting from the reversible phase transition between antiferroelectric and ferroelectric states, antiferroelectric materials have recently received widespread attentions for ...

Antiferroelectric thin films have properties ideal for energy storage due to their lower losses compared to their ferroelectric counterparts as well as their robust endurance ...

Energy storage density (ESD) values are regularly assessed for AFE and AFE-like, FE, and dielectric (DE) thin films. The reason for the "AFE-like" nomenclature in this work ...

1 ??· Antiferroelectric (Pb 0.87 Sr 0.05 Ba 0.05 La 0.02)(Zr 0.52 Sn 0.40 Ti 0.08)O 3 thin film capacitors were fabricated for dielectric energy storage. Thin films with excellent crystal quality (FWHM 0.021°) were prepared on (100) ...

In this paper, Pb 0.98 La 0.02 (Zr 0.55 Sn 0.45-x Ti x) 0.995 O 3 (x = 0.02-0.08) (PLZST) antiferroelectric (AFE) thick films were fabricated by a unique technology of the rolling ...

AgNbO 3-based antiferroelectric materials have attracted extensive attention in energy storage due to their double polarization-electric field hysteresis loops, but they always ...

Doped hafnium oxide films show good antiferroelectric (AFE) like properties that can be used for energy storage devices. In this paper, we propose the use of AFE silicon doped HfO 2 on a 3D ...

1 ??· Antiferroelectric (Pb 0.87 Sr 0.05 Ba 0.05 La 0.02)(Zr 0.52 Sn 0.40 Ti 0.08)O 3 thin film capacitors were fabricated for dielectric energy storage. Thin films with excellent crystal quality ...

The values of recoverable energy storage density of 32.6 J/cm 3 and efficiency of 88.1% are obtained for trilayer films annealed at 550 °C, meaning that the design of ...

been devoted to the development of high performance, antiferroelectric, energy storage ceramics and much progress has been achieved. In this review, the current state-of-the-art as regards ...